

Albert Chin

List of Publications by Year in descending order

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375
papers

7,483
citations

61984

43
h-index

110387

64
g-index

375
all docs

375
docs citations

375
times ranked

4642
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 1 | Electrical characteristics of high quality La ₂ O ₃ gate dielectric with equivalent oxide thickness of 5 /spl Aring/. IEEE Electron Device Letters, 2000, 21, 341-343. | 3.9 | 203 |
| 2 | N-Type Schottky Barrier Source/Drain MOSFET Using Ytterbium Silicide. IEEE Electron Device Letters, 2004, 25, 565-567. | 3.9 | 187 |
| 3 | High-density MIM capacitors using Al ₂ O ₃ and AlTiO _x dielectrics. IEEE Electron Device Letters, 2002, 23, 185-187. | 3.9 | 155 |
| 4 | Low-Power High-Performance Non-Volatile Memory on a Flexible Substrate with Excellent Endurance. Advanced Materials, 2011, 23, 902-905. | 21.0 | 130 |
| 5 | A high-density MIM capacitor (13 fF/1/4m/sup 2/) using ALD HfO ₂ dielectrics. IEEE Electron Device Letters, 2003, 24, 63-65. | 3.9 | 126 |
| 6 | Low-Voltage Steep Turn-On pMOSFET Using Ferroelectric High- κ Gate Dielectric. IEEE Electron Device Letters, 2014, 35, 274-276. | 3.9 | 112 |
| 7 | Alternative surface passivation on germanium for metal-oxide-semiconductor applications with high-k gate dielectric. Applied Physics Letters, 2004, 85, 4127-4129. | 3.3 | 110 |
| 8 | Low-Leakage-Current DRAM-Like Memory Using a One-Transistor Ferroelectric MOSFET With a Hf-Based Gate Dielectric. IEEE Electron Device Letters, 2014, 35, 138-140. | 3.9 | 110 |
| 9 | A TaN- κ HfO ₂ -Ge pMOSFET With Novel SiH ₄ Surface Passivation. IEEE Electron Device Letters, 2004, 25, 631-633. | 3.9 | 109 |
| 10 | Schottky-Barrier S/D MOSFETs With High- κ Gate Dielectrics and Metal-Gate Electrode. IEEE Electron Device Letters, 2004, 25, 268-270. | 3.9 | 99 |
| 11 | Deep levels and a possible d-x-like center in molecular beam epitaxial InAl _x As. Journal of Electronic Materials, 1987, 16, 271-274. | 2.2 | 95 |
| 12 | Germanium pMOSFETs with Schottky-barrier germanide S/D, high- κ gate dielectric and metal gate. IEEE Electron Device Letters, 2005, 26, 81-83. | 3.9 | 94 |
| 13 | High-Performance InGaZnO Thin-Film Transistors Using HfLaO Gate Dielectric. IEEE Electron Device Letters, 2009, 30, 1317-1319. | 3.9 | 86 |
| 14 | Quantum interference effects and spin-orbit interaction in quasi-one-dimensional wires and rings. Physical Review B, 1992, 46, 6846-6856. | 3.2 | 84 |
| 15 | Improvement of Voltage Linearity in High- κ MIM Capacitors Using HfO ₂ -SiO ₂ Stacked Dielectric. IEEE Electron Device Letters, 2004, 25, 538-540. | 3.9 | 84 |
| 16 | High-Performance SrTiO ₃ MIM Capacitors for Analog Applications. IEEE Transactions on Electron Devices, 2006, 53, 2312-2319. | 3.0 | 83 |
| 17 | High-Performance GaN MOSFET With High- κ LaAlO ₃ /SiO ₂ Gate Dielectric. IEEE Electron Device Letters, 2012, 33, 35-37. | 3.9 | 79 |
| 18 | Integrated antennas on Si, proton-implanted Si and Si-on-quartz. , 0, , . | | 72 |

| # | ARTICLE | IF | CITATIONS |
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| 19 | Very high-density (23 fF/ μm^2) RF MIM capacitors using high- κ TaTiO as the dielectric. IEEE Electron Device Letters, 2005, 26, 728-730. | 3.9 | 70 |
| 20 | Picosecond photoresponse of carriers in Si ion-implanted Si. Applied Physics Letters, 1996, 69, 653-655. | 3.3 | 69 |
| 21 | RF, DC, and reliability characteristics of ALD HfO ₂ /Al ₂ O ₃ laminate MIM capacitors for Si RF IC applications. IEEE Transactions on Electron Devices, 2004, 51, 886-894. | 3.0 | 69 |
| 22 | Integrated antennas on Si with over 100 GHz performance, fabricated using an optimized proton implantation process. IEEE Microwave and Wireless Components Letters, 2003, 13, 487-489. | 3.2 | 67 |
| 23 | Tuning effective metal gate work function by a novel gate dielectric HfLaO for nMOSFETs. IEEE Electron Device Letters, 2006, 27, 31-33. | 3.9 | 63 |
| 24 | Mechanism of GeO ₂ resistive switching based on the multi-phonon assisted tunneling between traps. Applied Physics Letters, 2012, 100, 243506. | 3.3 | 63 |
| 25 | High Density and Low Leakage Current in TiO_2 MIM Capacitors Processed at 300 °C. IEEE Electron Device Letters, 2008, 29, 845-847. | 3.9 | 62 |
| 26 | High performance ultra-low energy RRAM with good retention and endurance. , 2010, , . | | 61 |
| 27 | MIM capacitors using atomic-layer-deposited high- κ (HfO ₂) _{1-x} (Al ₂ O ₃) _x dielectrics. IEEE Electron Device Letters, 2003, 24, 60-62. | 3.9 | 60 |
| 28 | Small-Subthreshold-Swing and Low-Voltage Flexible Organic Thin-Film Transistors Which Use HfLaO as the Gate Dielectric. IEEE Electron Device Letters, 2009, 30, 133-135. | 3.9 | 59 |
| 29 | Oxide-based RRAM: Unified microscopic principle for both unipolar and bipolar switching. , 2011, , . | | 58 |
| 30 | PVD HfO ₂ for high-precision MIM capacitor applications. IEEE Electron Device Letters, 2003, 24, 387-389. | 3.9 | 57 |
| 31 | Wide V_{th} and V_{fb} Tunability for Metal-Gated MOS Devices With HfLaO Gate Dielectrics. IEEE Electron Device Letters, 2007, 28, 258-260. | 3.9 | 57 |
| 32 | Low-Voltage-Driven Flexible InGaZnO Thin-Film Transistor With Small Subthreshold Swing. IEEE Electron Device Letters, 2010, 31, 680-682. | 3.9 | 57 |
| 33 | Novel Ultra-low power RRAM with good endurance and retention. , 2010, , . | | 56 |
| 34 | High-performance MIM capacitor using ALD high- κ HfO ₂ -Al ₂ O ₃ laminate dielectrics. IEEE Electron Device Letters, 2003, 24, 730-732. | 3.9 | 55 |
| 35 | Physical and electrical characteristics of high- κ gate dielectric $\text{Hf}(\text{La}_x)\text{O}_y$. Solid-State Electronics, 2006, 50, 986-991. | 1.4 | 55 |
| 36 | Al_2O_3 -Ge-On-Insulator n- and p-MOSFETs With Fully NiSi and NiGe Dual Gates. IEEE Electron Device Letters, 2004, 25, 138-140. | 3.9 | 52 |

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| 37 | Comparison of MONOS Memory Device Integrity When Using $\text{Hf}_{1-x-y}\text{N}_x\text{O}_y$ Trapping Layers With Different N Compositions. IEEE Transactions on Electron Devices, 2008, 55, 1417-1423. | 3.0 | 52 |
| 38 | High-Temperature Leakage Improvement in Metal-Insulator-Metal Capacitors by Work-Function Tuning. IEEE Electron Device Letters, 2007, 28, 235-237. | 3.9 | 51 |
| 39 | Remarkably High Hole Mobility Metal-Oxide Thin-Film Transistors. Scientific Reports, 2018, 8, 889. | 3.3 | 51 |
| 40 | Electrical characteristics and suppressed boron penetration behavior of thermally stable HfTaO gate dielectrics with polycrystalline-silicon gate. Applied Physics Letters, 2004, 85, 2893-2895. | 3.3 | 49 |
| 41 | Smooth Muscle Cell Genome Browser: Enabling the Identification of Novel Serum Response Factor Target Genes. PLoS ONE, 2015, 10, e0133751. | 2.5 | 48 |
| 42 | Adjunctive Intraoperative Arterial Dilation. Archives of Surgery, 1981, 116, 1391. | 2.2 | 47 |
| 43 | Oxygen Vacancy in Hafnia as a Blue Luminescence Center and a Trap of Charge Carriers. Journal of Physical Chemistry C, 2016, 120, 19980-19986. | 3.1 | 47 |
| 44 | Tuning the Morphology of Isoindigo Donor-Acceptor Polymer Film for High Sensitivity Ammonia Sensor. Advanced Functional Materials, 2018, 28, 1803145. | 14.9 | 47 |
| 45 | Improved High-Temperature Leakage in High-Density MIM Capacitors by Using a TiLaO Dielectric and an Ir Electrode. IEEE Electron Device Letters, 2007, 28, 1095-1097. | 3.9 | 46 |
| 46 | Low Subthreshold Swing HfLaO/Pentacene Organic Thin-Film Transistors. IEEE Electron Device Letters, 2008, 29, 215-217. | 3.9 | 46 |
| 47 | High-performance poly-silicon TFTs incorporating LaAlO_3 as the gate dielectric. IEEE Electron Device Letters, 2005, 26, 384-386. | 3.9 | 45 |
| 48 | $\text{Ni/GeO}_2/\text{TiO}_2/\text{TaN}$ RRAM on Flexible Substrate With Excellent Resistance Distribution. IEEE Electron Device Letters, 2013, 34, 505-507. | 3.9 | 45 |
| 49 | 40-GHz coplanar waveguide bandpass filters on silicon substrate. IEEE Microwave and Wireless Components Letters, 2002, 12, 429-431. | 3.2 | 44 |
| 50 | Fully Silicided NiSi:Hf-LaAlO ₃ GOI n-MOSFETs With High Electron Mobility. IEEE Electron Device Letters, 2004, 25, 559-561. | 3.9 | 44 |
| 51 | A flexible organic pentacene nonvolatile memory based on high- ϵ^r dielectric layers. Applied Physics Letters, 2008, 93, . | 3.3 | 44 |
| 52 | Remarkably high mobility ultra-thin-film metal-oxide transistor with strongly overlapped orbitals. Scientific Reports, 2016, 6, 19023. | 3.3 | 44 |
| 53 | Frequency-dependent capacitance reduction in high-k AlTiO_x and Al_2O_3 gate dielectrics from IF to RF frequency range. IEEE Electron Device Letters, 2002, 23, 203-205. | 3.9 | 43 |
| 54 | Fabrication of very high resistivity Si with low loss and cross talk. IEEE Electron Device Letters, 2000, 21, 442-444. | 3.9 | 42 |

| # | ARTICLE | IF | CITATIONS |
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| 55 | Effect of annealing temperature on physical and electrical properties of Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ thin films on Al ₂ O ₃ -buffered Si. Applied Physics Letters, 2002, 80, 1984-1986. | 3.3 | 41 |
| 56 | Improved Capacitance Density and Reliability of High- κ Ni/ZrO ₂ /TiN MIM Capacitors Using Laser-Annealing Technique. IEEE Electron Device Letters, 2010, 31, 749-751. | 3.9 | 41 |
| 57 | A Novel Read Scheme for Large Size One-Resistor Resistive Random Access Memory Array. Scientific Reports, 2017, 7, 42375. | 3.3 | 41 |
| 58 | Achievement of exceptionally high mobilities in modulation-doped Ga _{1-x} In _x As on InP using a stress compensated structure. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1990, 8, 364. | 1.6 | 40 |
| 59 | A Nonvolatile InGaZnO Charge-Trapping-Engineered Flash Memory With Good Retention Characteristics. IEEE Electron Device Letters, 2010, 31, 201-203. | 3.9 | 40 |
| 60 | Origin of traps and charge transport mechanism in hafnia. Applied Physics Letters, 2014, 105, 222901. | 3.3 | 38 |
| 61 | Ultralow Switching Energy Ni/GeO _x /HfON/TaN RRAM. IEEE Electron Device Letters, 2011, 32, 366-368. | 3.9 | 37 |
| 62 | Use of a High-Work-Function Ni Electrode to Improve the Stress Reliability of Analog SrTiO ₃ Metal-Insulator-Metal Capacitors. IEEE Electron Device Letters, 2007, 28, 694-696. | 3.9 | 36 |
| 63 | Design of Dual-Passband Microstrip Bandpass Filters With Multi-Spurious Suppression. IEEE Microwave and Wireless Components Letters, 2010, 20, 199-201. | 3.2 | 36 |
| 64 | Transmission line noise from standard and proton-implanted Si. , 0, , . | | 35 |
| 65 | Modeling Study of the Impact of Surface Roughness on Silicon and Germanium UTB MOSFETs. IEEE Transactions on Electron Devices, 2005, 52, 2430-2439. | 3.0 | 35 |
| 66 | High- κ Ir/TiTaO/TaN capacitors suitable for analog IC applications. IEEE Electron Device Letters, 2005, 26, 504-506. | 3.9 | 35 |
| 67 | Optical Properties of TiO ₂ Films Deposited by Reactive Electron Beam Sputtering. Journal of Electronic Materials, 2017, 46, 6089-6095. | 2.2 | 35 |
| 68 | Summary Abstract: Material properties and clustering in molecular-beam epitaxial In _{0.52} Al _{0.48} As and In _{1-x} As _y GaxAl _y As. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 800. | 1.6 | 34 |
| 69 | High-Density and Low-Leakage-Current MIM Capacitor Using Stacked TiO ₂ /ZrO ₂ Insulators. IEEE Electron Device Letters, 2009, 30, 715-717. | 3.9 | 34 |
| 70 | A Low-Power K-Band CMOS VCO With Four-Coil Transformer Feedback. IEEE Microwave and Wireless Components Letters, 2010, 20, 459-461. | 3.2 | 34 |
| 71 | Long-Endurance Nanocrystal TiO ₂ Resistive Memory Using a TaON Buffer Layer. IEEE Electron Device Letters, 2011, 32, 1749-1751. | 3.9 | 34 |
| 72 | Remarkably High Mobility Thin-Film Transistor on Flexible Substrate by Novel Passivation Material. Scientific Reports, 2017, 7, 1147. | 3.3 | 34 |

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| 73 | Thin oxides with in situ native oxide removal [n-MOSFETs]. IEEE Electron Device Letters, 1997, 18, 417-419. | 3.9 | 33 |
| 74 | High quality $\text{La}_{2/3}\text{O}_3$ and $\text{Al}_{2/3}\text{O}_3$ gate dielectrics with equivalent oxide thickness 5-10 Å, . , O, , . | | 33 |
| 75 | Very high density RF MIM capacitors ($17 \text{ fF}/\mu\text{m}^2$) using high- κ $\text{Al}_{2/3}\text{O}_3$ doped $\text{Ta}_{2/3}\text{O}_5$ dielectrics. IEEE Microwave and Wireless Components Letters, 2003, 13, 431-433. | 3.2 | 33 |
| 76 | Evidence and Understanding of ALD HfO_2 - Al_2O_3 Laminate MIM Capacitors Outperforming Sandwich Counterparts. IEEE Electron Device Letters, 2004, 25, 681-683. | 3.9 | 33 |
| 77 | A Dual-Resonant Mode 10/22-GHz VCO With a Novel Inductive Switching Approach. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 2165-2177. | 4.6 | 32 |
| 78 | Device and reliability of high- κ $\text{Al}_{2/3}\text{O}_3$ gate dielectric with good mobility and low D_{it} , . , O, , . | | 31 |
| 79 | RF passive devices on Si with excellent performance close to ideal devices designed by electro-magnetic simulation. , O, , . | | 31 |
| 80 | Electron mobility in Ge and strained-Si channel ultrathin-body metal-oxide semiconductor field-effect transistors. Applied Physics Letters, 2004, 85, 2402-2404. | 3.3 | 31 |
| 81 | Low temperature MOSFET technology with Schottky barrier source/drain, high- κ gate dielectric and metal gate electrode. Solid-State Electronics, 2004, 48, 1987-1992. | 1.4 | 31 |
| 82 | Metal-insulator-metal RF bypass capacitor using niobium oxide ($\text{Nb}_{2/3}\text{O}_5$) with $\text{HfO}_2/\text{Al}_{2/3}\text{O}_3$ barriers. IEEE Electron Device Letters, 2005, 26, 625-627. | 3.9 | 31 |
| 83 | $\text{Bi}_{3.25}\text{La}_{0.75}\text{Ti}_3\text{O}_{12}$ thin films on ultrathin Al_2O_3 buffered Si for ferroelectric memory application. Applied Physics Letters, 2002, 80, 3168-3170. | 3.3 | 30 |
| 84 | Subpicosecond carrier response of unannealed low-temperature-grown GaAs vs temperature. Journal of Electronic Materials, 1993, 22, 1461-1464. | 2.2 | 29 |
| 85 | The effect of native oxide on thin gate oxide integrity. IEEE Electron Device Letters, 1998, 19, 426-428. | 3.9 | 29 |
| 86 | Fully silicided NiSi gate on La_2O_3 MOSFETs. IEEE Electron Device Letters, 2003, 24, 348-350. | 3.9 | 29 |
| 87 | Stacked $\text{GeO}/\text{SrTiO}_x$ Resistive Memory with Ultralow Resistance Currents. Applied Physics Letters, 2011, 98, . | 3.3 | 29 |
| 88 | Charge transport in amorphous $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$. Applied Physics Letters, 2015, 106, . | 3.3 | 29 |
| 89 | Formation of Ni germano-silicide on single crystalline $\text{Si}_{0.3}\text{Ge}_{0.7}/\text{Si}$. IEEE Electron Device Letters, 2002, 23, 464-466. | 3.9 | 28 |
| 90 | Very Low Voltage $\text{SiO}_2/\text{HfON}/\text{HfAlO}/\text{TaN}$ Memory with Fast Speed and Good Retention. , 2006, , . | | 28 |

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| 91 | Investigation of performance limits of germanium double-gated MOSFETs. , 0, , . | | 27 |
| 92 | Three-dimensional metal gate-high- κ -GOI CMOSFETs on 1-poly-6-metal 0.18- μ m Si devices. IEEE Electron Device Letters, 2005, 26, 118-120. | 3.9 | 27 |
| 93 | Very high K and high density TiTaO MIM capacitors for analog and RF applications. , 0, , . | | 27 |
| 94 | Thermal Leakage Improvement by Using a High-Work-Function Ni Electrode in High- κ TiHfO Metal-Insulator-Metal Capacitors. Journal of the Electrochemical Society, 2007, 154, G54. | 2.9 | 26 |
| 95 | Memristor effect in GeO[SiO ₂] and GeO[SiO] solid alloys films. Applied Physics Letters, 2019, 114, . | 3.3 | 26 |
| 96 | Fully silicided NiSi and germanided NiGe dual gates on SiO ₂ n- and p-MOSFETs. IEEE Electron Device Letters, 2003, 24, 739-741. | 3.9 | 25 |
| 97 | High-density MIM capacitors using AlTaOx dielectrics. IEEE Electron Device Letters, 2003, 24, 306-308. | 3.9 | 25 |
| 98 | All Nonmetal Resistive Random Access Memory. Scientific Reports, 2019, 9, 6144. | 3.3 | 24 |
| 99 | High Performance All Nonmetal SiNx Resistive Random Access Memory with Strong Process Dependence. Scientific Reports, 2020, 10, 2807. | 3.3 | 24 |
| 100 | The effect of native oxide on epitaxial SiGe from deposited amorphous Ge on Si. Applied Physics Letters, 1999, 74, 528-530. | 3.3 | 23 |
| 101 | The performance limiting factors as RF MOSFETs scale down. , 0, , . | | 23 |
| 102 | Novel SiO ₂ /AlN/HfAlO ₂ /IrO ₂ memory with fast erase, large V_{TH} and good retention. , 0, , . | | 23 |
| 103 | New Material Transistor with Record-High Field-Effect Mobility among Wide-Band-Gap Semiconductors. ACS Applied Materials & Interfaces, 2016, 8, 19187-19191. | 8.0 | 23 |
| 104 | Fully silicided NiSi and germanided NiGe dual gates on SiO ₂ /Si and Al ₂ O ₃ /Ge-on-insulator MOSFETs. , 0, , . | | 22 |
| 105 | Growth of GaAs on SiO ₂ by molecular-beam epitaxy. Journal of Applied Physics, 1987, 62, 1416-1419. | 2.5 | 21 |
| 106 | Strong accumulation of As precipitates in low temperature InGaAs quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 1994, 64, 1546-1548. | 3.3 | 21 |
| 107 | RF loss and crosstalk on extremely high resistivity (10 k Ω -cm) Si fabricated by ion implantation. , 0, , . | | 21 |
| 108 | Interfacial layer dependence on device property of high- κ TiLaO Ge/Si N-type metal-oxide-semiconductor capacitors at small equivalent-oxide thickness. Applied Physics Letters, 2009, 95, . | 3.3 | 21 |

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| 109 | Charge transport mechanism in SiNx-based memristor. Applied Physics Letters, 2019, 115, 253502. | 3.3 | 21 |
| 110 | Charge transport mechanism in the forming-free memristor based on silicon nitride. Scientific Reports, 2021, 11, 2417. | 3.3 | 21 |
| 111 | Comparison of high quality (111)B and (100) AlGaAs grown by molecular beam epitaxy. Applied Physics Letters, 1991, 59, 2394-2396. | 3.3 | 20 |
| 112 | Lanthanide (Tb)-doped HfO ₂ for high-density MIM capacitors. IEEE Electron Device Letters, 2003, 24, 442-444. | 3.9 | 20 |
| 113 | Very low defects and high performance Ge-on-insulator p-MOSFETs with Al ₂ O ₃ gate dielectrics. , 0, , . | | 20 |
| 114 | Mobility Enhancement in TaN Metal-Gate MOSFETs Using Tantalum Incorporated HfO ₂ Gate Dielectric. IEEE Electron Device Letters, 2004, 25, 501-503. | 3.9 | 20 |
| 115 | Nanoscale potential fluctuation in non-stoichiometric HfO _x and low resistive transport in RRAM. Microelectronic Engineering, 2015, 147, 165-167. | 2.4 | 20 |
| 116 | Raman scattering by optical phonons in In _{1-x} Al _x As lattice matched to InP. Applied Physics Letters, 1988, 53, 1652-1653. | 3.3 | 19 |
| 117 | 3D GOI CMOSFETs with novel IrO ₂ (Hf) dual gates and high-K dielectric on 1P6M-0.18 μ m-CMOS. , 0, , . | | 19 |
| 118 | Strain-induced very low noise RF MOSFETs on flexible plastic substrate. , 0, , . | | 19 |
| 119 | Dual Metal Gates with Band-Edge Work Functions on Novel HfLaO High-K Gate Dielectric. , 0, , . | | 19 |
| 120 | High Temperature Stable [Ir ₃ Si-TaN]/HfLaON CMOS with Large Work-Function Difference. , 2006, , . | | 19 |
| 121 | Improvement of the Performance of TiHfO MIM Capacitors by Using a Dual Plasma Treatment of the Lower Electrode. IEEE Electron Device Letters, 2008, 29, 1105-1107. | 3.9 | 19 |
| 122 | Highly-scaled 3.6-nm ENT trapping layer MONOS device with good retention and endurance. , 2010, , . | | 19 |
| 123 | Bipolar conductivity in amorphous HfO ₂ . Applied Physics Letters, 2011, 99, . | 3.3 | 19 |
| 124 | An Offset Readout Current Sensing Scheme for One-Resistor RRAM-Based Cross-Point Array. IEEE Electron Device Letters, 2019, 40, 208-211. | 3.9 | 19 |
| 125 | In _{0.52} Al _{0.48} As/InAs/In _x Al _{1-x} As pseudomorphic HEMT's on InP. IEEE Electron Device Letters, 1997, 18, 157-159. | 3.9 | 18 |
| 126 | Improved electrical characteristics of CoSi ₂ using HF-vapor pretreatment. IEEE Electron Device Letters, 1999, 20, 200-202. | 3.9 | 18 |

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| 127 | High temperature formed SiGe p-MOSFETs with good device characteristics. IEEE Electron Device Letters, 2000, 21, 350-352. | 3.9 | 18 |
| 128 | Low RF noise and power loss for ion-implanted Si having an improved implantation process. IEEE Electron Device Letters, 2003, 24, 28-30. | 3.9 | 18 |
| 129 | Large Q-factor improvement for spiral inductors on silicon using proton implantation. IEEE Microwave and Wireless Components Letters, 2003, 13, 460-462. | 3.2 | 18 |
| 130 | Narrow-band band-pass filters on silicon substrates at 30 GHz. , 0, , . | | 18 |
| 131 | Electrical-stress effects and device modeling of 0.18- μm RF MOSFETs. IEEE Transactions on Electron Devices, 2006, 53, 636-642. | 3.0 | 18 |
| 132 | Low-Threshold-Voltage MoN/HfAlO/SiON p-MOSFETs With 0.85-nm EOT. IEEE Electron Device Letters, 2009, 30, 861-863. | 3.9 | 18 |
| 133 | Ultralow-Power Ni/GeO/STO/TaN Resistive Switching Memory. IEEE Electron Device Letters, 2010, 31, 1020-1022. | 3.9 | 18 |
| 134 | Charge transport in thin hafnium and zirconium oxide films. Optoelectronics, Instrumentation and Data Processing, 2017, 53, 184-189. | 0.6 | 18 |
| 135 | Charge transport mechanism of high-resistive state in RRAM based on SiO _x . Applied Physics Letters, 2019, 114, . | 3.3 | 18 |
| 136 | Exceedingly High Performance Top-Gate P-Type SnO Thin Film Transistor with a Nanometer Scale Channel Layer. Nanomaterials, 2021, 11, 92. | 4.1 | 18 |
| 137 | The Strong Degradation of 30 \AA Gate Oxide Integrity Contaminated by Copper. Journal of the Electrochemical Society, 2001, 148, F73. | 2.9 | 17 |
| 138 | The potential of functional scaling. IEEE Circuits and Devices: the Magazine of Electronic and Photonic Systems, 2005, 21, 27-35. | 0.4 | 17 |
| 139 | A Low-Power Current-Reuse LNA for Ultra-Wideband Wireless Receivers from 3.1 to 10.6 GHz. , 2007, , . | | 17 |
| 140 | Modeling finger number dependence on RF noise to 10 GHz in 0.13 μm node MOSFETs with 80nm gate length. , 0, , . | | 16 |
| 141 | Low voltage high speed SiO ₂ /AlGaIn/AlLaO ₃ /TaIn memory with good retention. , 2005, , . | | 16 |
| 142 | High work function Ir/Si gates on HfAlON p-MOSFETs. IEEE Electron Device Letters, 2006, 27, 90-92. | 3.9 | 16 |
| 143 | Study of parallel coupled-line microstrip filter in broadband. Microwave and Optical Technology Letters, 2006, 48, 373-375. | 1.4 | 16 |
| 144 | Higher Gate Capacitance Ge n-MOSFETs Using Laser Annealing. IEEE Electron Device Letters, 2011, 32, 449-451. | 3.9 | 16 |

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| 145 | Improved Device Distribution in High-Performance SiNx Resistive Random Access Memory via Arsenic Ion Implantation. <i>Nanomaterials</i> , 2021, 11, 1401. | 4.1 | 16 |
| 146 | High-performance microwave coplanar bandpass and bandstop filters on Si substrates. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2003, 51, 2036-2040. | 4.6 | 15 |
| 147 | The minimum noise figure and mechanism as scaling RF MOSFETs from 0.18 to 0.13 μ m technology nodes. , 0, , . | | 15 |
| 148 | Impact of surface roughness on silicon and germanium ultra-thin-body MOSFETs. , 0, , . | | 15 |
| 149 | A novel program-erasable high- κ /AlN-Si MIS capacitor. <i>IEEE Electron Device Letters</i> , 2005, 26, 148-150. | 3.9 | 15 |
| 150 | High Performance Micro-Crystallized TaN/SrTiO ₃ /TaN Capacitors for Analog and RF Applications. , 2006, , . | | 15 |
| 151 | Improved Stress Reliability of Analog TiHfO Metal-Insulator-Metal Capacitors Using High-Work-Function Electrode. <i>Japanese Journal of Applied Physics</i> , 2007, 46, 7300. | 1.5 | 15 |
| 152 | Highly scaled charge-trapping layer of ZrON nonvolatile memory device with good retention. <i>Applied Physics Letters</i> , 2010, 97, . | 3.3 | 15 |
| 153 | Arsenic-Implanted HfON Charge-Trapping Flash Memory With Large Memory Window and Good Retention. <i>IEEE Electron Device Letters</i> , 2011, 32, 381-383. | 3.9 | 15 |
| 154 | Transapical beating heart cardioscopy technique for off-pump visualization of heart valves. <i>Journal of Thoracic and Cardiovascular Surgery</i> , 2012, 144, 231-234. | 0.8 | 15 |
| 155 | Percolation conductivity in hafnium sub-oxides. <i>Applied Physics Letters</i> , 2014, 105, 262903. | 3.3 | 15 |
| 156 | RF MIM capacitors using high-K Al ₂ O ₃ and AlTiO _x dielectrics. , 0, , . | | 14 |
| 157 | Traps in molecular-beam epitaxial In _{0.53} (Ga _x Al _{1-x}) _{0.47} As/InP. <i>Journal of Applied Physics</i> , 1990, 67, 2450-2453. | 2.5 | 14 |
| 158 | Spontaneous formation of Al rich and Ga rich Al _x Ga _{1-x} As/Al _y Ga _{1-y} As superlattice and strong enhancement of optical properties. <i>Applied Physics Letters</i> , 1994, 65, 1921-1923. | 3.3 | 14 |
| 159 | RF noise in 0.18- μ m and 0.13- μ m MOSFETs. <i>IEEE Microwave and Wireless Components Letters</i> , 2002, 12, 464-466. | 3.2 | 14 |
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